

Jean-Baptiste Leran

List of Publications by Year in descending order

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papers

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citations

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20
docs citations

20
times ranked

353
citing authors

#	ARTICLE	IF	CITATIONS
1	Bistability of Contact Angle and Its Role in Achieving Quantum-Thin Self-Assisted GaAs nanowires. Nano Letters, 2018, 18, 49-57.	9.1	62
2	Impact of the Ga Droplet Wetting, Morphology, and Pinholes on the Orientation of GaAs Nanowires. Crystal Growth and Design, 2016, 16, 5781-5786.	3.0	38
3	Optimizing the yield of A-polar GaAs nanowires to achieve defect-free zinc blende structure and enhanced optical functionality. Nanoscale, 2018, 10, 17080-17091.	5.6	31
4	III-V Integration on Si(100): Vertical Nanospades. ACS Nano, 2019, 13, 5833-5840.	14.6	24
5	van der Waals Epitaxy of Earth-Abundant Zn ₃ P ₂ on Graphene for Photovoltaics. Crystal Growth and Design, 2020, 20, 3816-3825.	3.0	24
6	Multiple morphologies and functionality of nanowires made from earth-abundant zinc phosphide. Nanoscale Horizons, 2020, 5, 274-282.	8.0	15
7	Towards defect-free thin films of the earth-abundant absorber zinc phosphide by nanopatterning. Nanoscale Advances, 2021, 3, 326-332.	4.6	13
8	Raman spectroscopy and lattice dynamics calculations of tetragonally-structured single crystal zinc phosphide (Zn ₃ P ₂) nanowires. Nanotechnology, 2021, 32, 085704.	2.6	10
9	The path towards 1 μm monocrystalline Zn ₃ P ₂ films on InP: substrate preparation, growth conditions and luminescence properties. JPhys Energy, 2021, 3, 034011.	5.3	8
10	Molecular beam epitaxy of InAs nanowires in SiO ₂ nanotube templates: challenges and prospects for integration of III-Vs on Si. Nanotechnology, 2016, 27, 455601.	2.6	7
11	Heterotwin Zn ₃ P ₂ superlattice nanowires: the role of indium insertion in the superlattice formation mechanism and their optical properties. Nanoscale, 2020, 12, 22534-22540.	5.6	7
12	Rotated domains in selective area epitaxy grown Zn ₃ P ₂ : formation mechanism and functionality. Nanoscale, 2021, 13, 18441-18450.	5.6	7
13	Showcasing the optical properties of monocrystalline zinc phosphide thin films as an earth-abundant photovoltaic absorber. Materials Advances, 2022, 3, 1295-1303.	5.4	7
14	Tilting Catalyst-Free InAs Nanowires by 3D-Twinning and Unusual Growth Directions. Crystal Growth and Design, 2017, 17, 3596-3605.	3.0	4
15	GaAs nanowires on Si nanopillars: towards large scale, phase-engineered arrays. Nanoscale Horizons, 2022, 7, 211-219.	8.0	4
16	Nanoscale Growth Initiation as a Pathway to Improve the Earth-Abundant Absorber Zinc Phosphide. ACS Applied Energy Materials, 2022, 5, 5298-5306.	5.1	3
17	Raman tensor of zinc-phosphide (Zn ₃ P ₂): from polarization measurements to simulation of Raman spectra. Physical Chemistry Chemical Physics, 2021, 24, 63-72.	2.8	3
18	van der Waals Epitaxy of Co ₁₀ X ₁₀ Zn ₁₀ Mn _x Y _i Thin Films: Chemical Composition Engineering and Magnetic Properties. Journal of Physical Chemistry C, 2021, 125, 9391-9399.	3.1	1

#	ARTICLE	IF	CITATIONS
19	Modeling the Shape Evolution of Selective Area Grown Zn ₃ P ₂ Nanoislands. Crystal Growth and Design, 2021, 21, 4732-4737.	3.0	1
20	Nanoscale Mapping of Light Emission in Nanospade-Based InGaAs Quantum Wells Integrated on Si(100): Implications for Dual Light-Emitting Devices. ACS Applied Nano Materials, 2022, 5, 5508-5515.	5.0	0